

Supporting Information

A crosslinked fullerene matrix doped with an ionic fullerene as a cathodic buffer layer toward high-performance and thermally stable polymer and organic metalhalide perovskite solar cells

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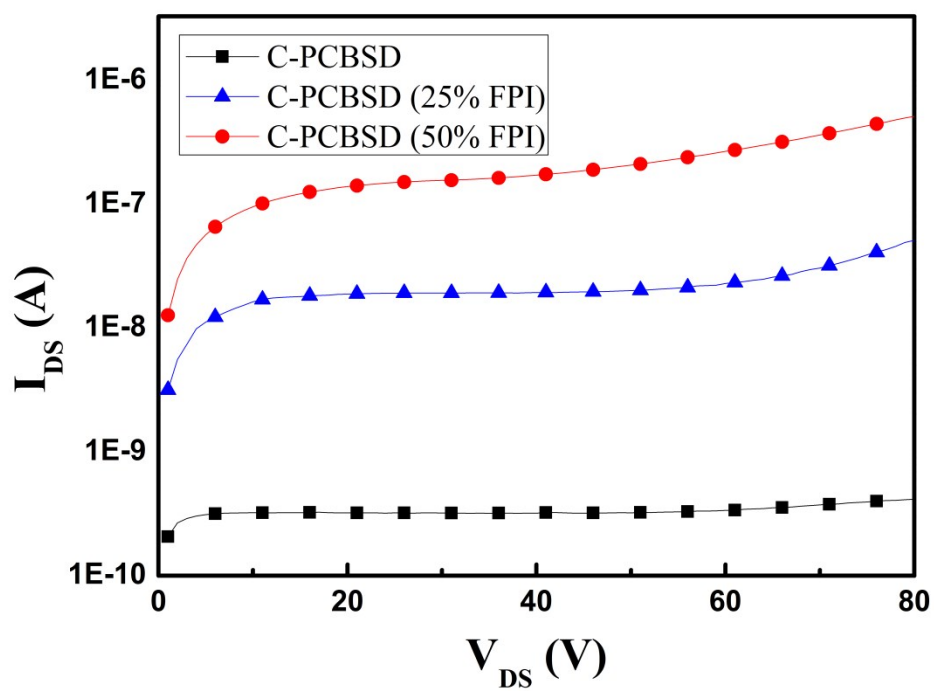


Figure S1. N-type OFET electrical characteristic of C-PCBSD films at varied dopant concentration

Table S1. Summary of OFET device performance of C-PCBSD with varying FPI dopant concentration

Material	Electron mobility ($\text{cm}^2 \text{V}^{-1} \text{s}^{-1}$)
C-PCBSD	1.3×10^{-5}
C-PCBSD (FPI, 25%)	2.4×10^{-5}
C-PCBSD (FPI, 50%)	6.0×10^{-5}